

REPLACEMENT CLAIMS

13. The semiconductor structure of claim 10, wherein the dielectric layer has a concentration of nitrogen which is higher in a center portion of the dielectric layer as compared to portions adjacent both the first conductive layer and the second conductive layer.
42. (Amended) A semiconductor structure, comprising
a semiconductor substrate; and
a dielectric feature comprising [titanium] lanthanum, aluminum, nitrogen, and oxygen
over the semiconductor substrate.